IX-01
www.oxfordplasma.de/process/inasalsb.htm

OXFORD INSTRUMENTS

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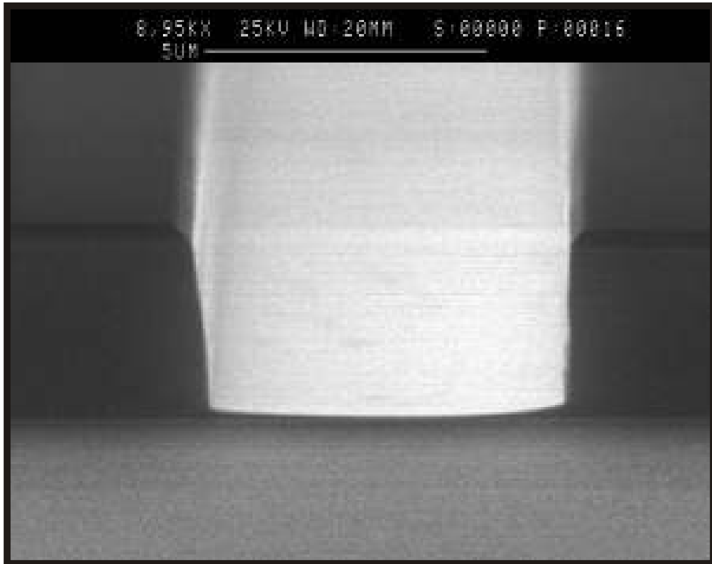
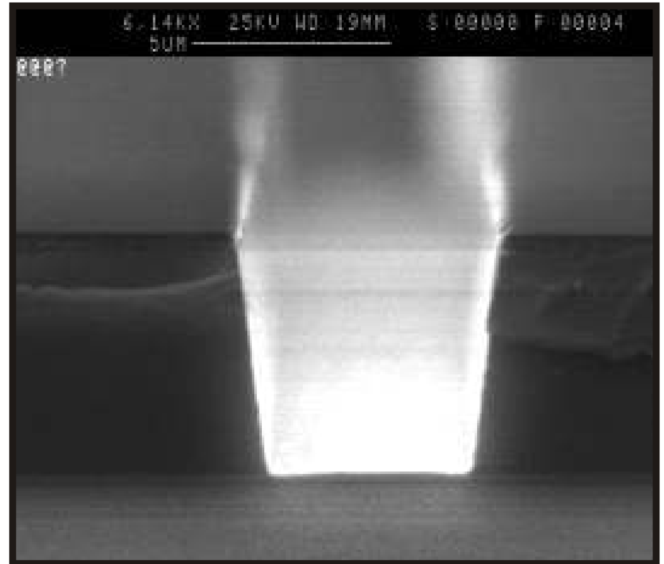
Plasmalab Data

InAs/ AlSb ICP Etching



OPT application lab:
4.5 µm deep InAs/ AlSb etch, SiCl4 based

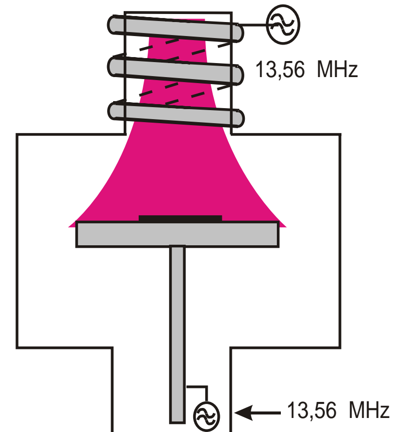


OPT application lab:
5.5 µm deep InAs/ AlSb etch, Cl2 based

Plasmalab 80 Plus

Plasmalab System 100

Plasmalab System 133



Technology:
Reactive Ion Etching
with ICP Source (2 or 13 MHz)
Inductive Coupled Plasma
RF driven substrate electrode

Results:
Rate : 0.7 - 0.9 µm/ min
selectivity to SiO2 mask 6 - 12 : 1
good uniformity
smooth surface